

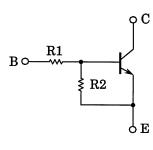
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

RN1101F,RN1102F,RN1103F RN1104F,RN1105F,RN1106F

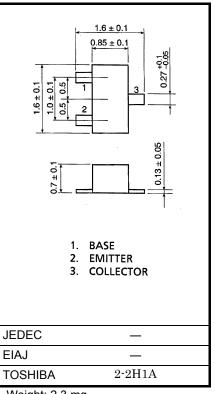
Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2101F~RN2106F

Equivalent Circuit And Bias Resister Values



| Type No. | R1 (kΩ) | R2 (kΩ) |
|----------|---|---|
| RN1101F | 4.7 | 4.7 |
| RN1102F | 10 | 10 |
| RN1103F | 22 | 22 |
| RN1104F | 47 | 47 |
| RN1105F | 2.2 | 47 |
| RN1106F | 4.7 | 47 |
| | RN1101F RN1102F RN1103F RN1104F RN1105F | RN1101F 4.7 RN1102F 10 RN1103F 22 RN1104F 47 RN1105F 2.2 |



Absolute Maximum Ratings (Ta = 25°C)

| weight. | 2.3 | mg | |
|---------|-----|----|--|
| | | | |

| Characteris | Symbol | Rating | Unit | | |
|-----------------------------|----------------|------------------|---------|----|--|
| Collector-base voltage | RN1101F~1106F | V _{CBO} | 50 | V | |
| Collector-emitter voltage | | V _{CEO} | 50 | V | |
| Emitter-base voltage | RN1101F~1104F | V _{FBO} | 10 | V | |
| Emilier-base voltage | RN1105F, 1106F | ▲EBO | 5 | | |
| Collector current | | Ι _C | 100 | mA | |
| Collector power dissipation | RN1101F~1106F | P _C | 100 | mW | |
| Junction temperature | RN1101F~1100F | Tj | 150 | °C | |
| Storage temperature range | | T _{stg} | -55~150 | °C | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

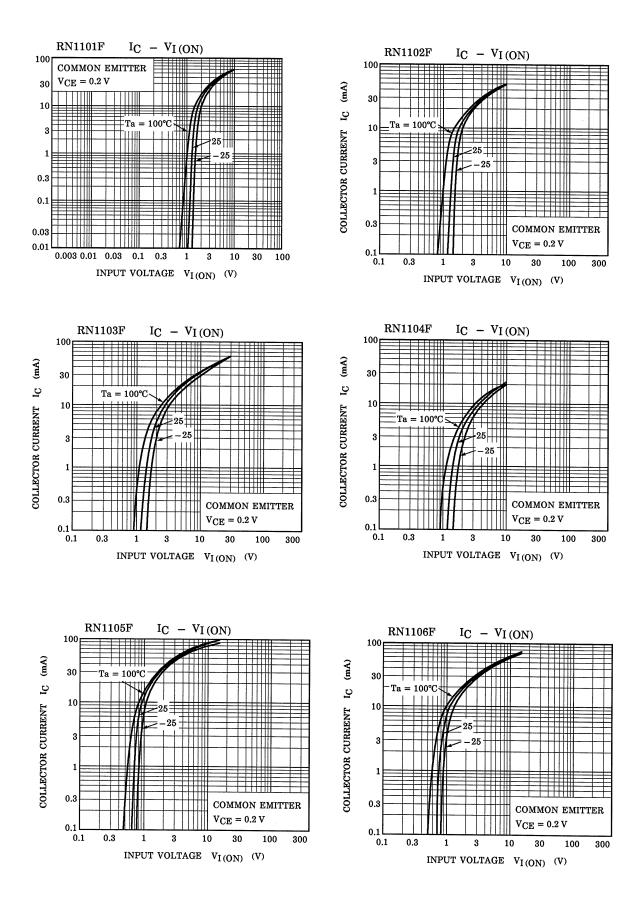
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit in mm

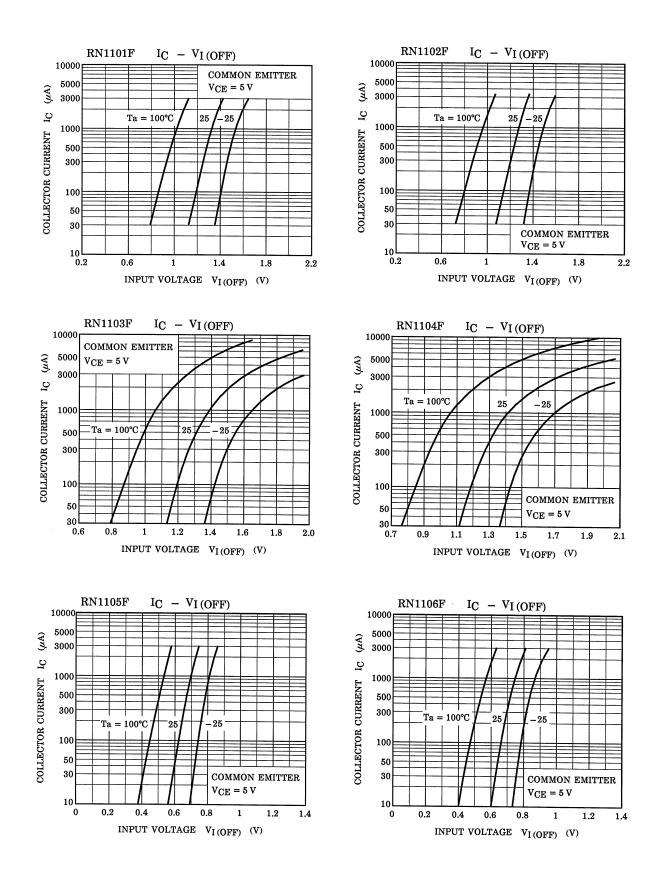
Electrical Characteristics (Ta = 25°C)

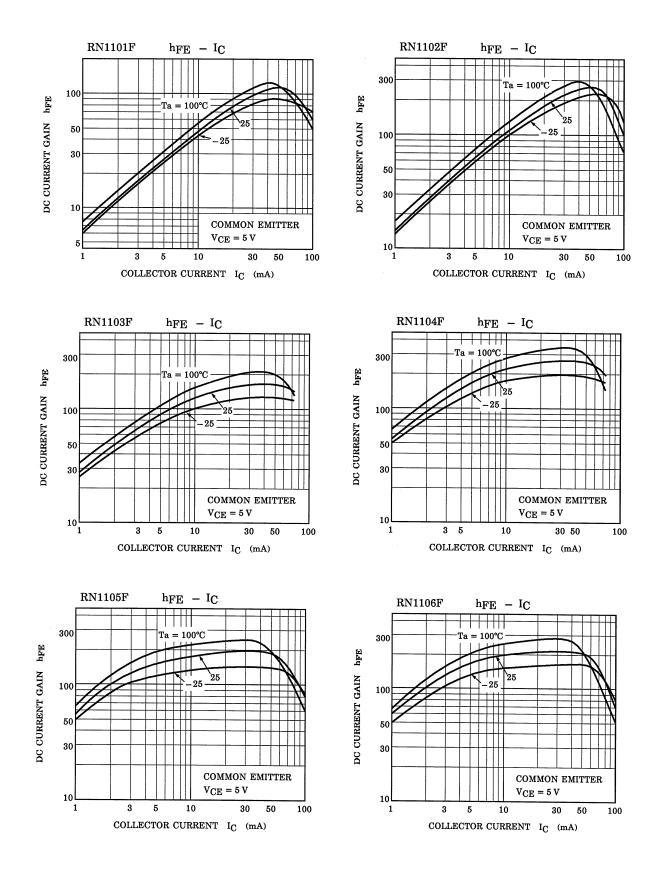
| Character | istic | Symbol | Test Circuit | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|-------------------|-----------------------|-----------------|--|--------|--------|-------|------|
| Collector cut-off current | RN1101F | I _{CBO} | | V _{CB} = 50V, I _E = 0 | — | - | 100 | nA |
| | ~1106F | | | V _{CE} = 50V, I _B = 0 | _ | - | 500 | |
| Emitter cut-off current | RN1101F | I _{EBO} | _ | V _{EB} = 10V, I _C = 0 | 0.82 | _ | 1.52 | mA |
| | RN1102F | | | | 0.38 | _ | 0.71 | |
| | RN1103F | | | | 0.17 | _ | 0.33 | |
| | RN1104F | | | | 0.082 | _ | 0.15 | |
| | RN1105F | | | | 0.078 | _ | 0.145 | |
| | RN1106F | | | $V_{EB} = 5V, I_C = 0$ | 0.074 | _ | 0.138 | |
| | RN1101F | | | | 30 | _ | _ | |
| | RN1102F | | | | 50 | _ | _ | |
| | RN1103F | L. | | | 70 | _ | _ | |
| DC current gain | RN1104F | h _{FE} | _ | V _{CE} = 5V, I _C = 10mA | 80 | _ | _ | _ |
| | RN1105F | | | | 80 | _ | _ | |
| | RN1106F | | | | 80 | _ | _ | |
| Collector-emitter saturation voltage | RN1101F ~1106F | V _{CE (sat)} | _ | I _C = 5mA, I _B = 0.25mA | _ | 0.1 | 0.3 | V |
| | RN1101F | VI (ON) | | V _{CE} = 0.2V, I _C = 5mA | 1.1 | _ | 2.0 | v |
| Input voltage (ON) | RN1102F | | _ | | 1.2 | _ | 2.4 | |
| | RN1103F | | | | 1.3 | _ | 3.0 | |
| | RN1104F | | | | 1.5 | _ | 5.0 | |
| | RN1105F | | | | 0.6 | _ | 1.1 | |
| | RN1106F | | | | 0.7 | _ | 1.3 | |
| Input voltage (OFF) | RN1101F ~1104F | | _ | V _{CE} = 5V, I _C = 0.1mA | 1.0 | _ | 1.5 | v |
| | RN1105F, 1106F | VI (OFF) | | | 0.5 | _ | 0.8 | |
| Transition frequency | RN1101F ~1106F | fT | _ | V _{CE} = 10V, I _C = 5mA | _ | 250 | _ | MHz |
| Collector Output capacitance | RN1101F ~1106F | C _{ob} | _ | $V_{CB} = 10V, I_E = 0,$ f = 1MH _z | _ | 3 | 6 | pF |
| | RN1101F | 2F 3F R1 — | | _ | 3.29 | 4.7 | 6.11 | |
| | RN1102F | | | | 7 | 10 | 13 | kΩ |
| lanut naciatan | RN1103F | | | | 15.4 | 22 | 28.6 | |
| Input resistor | RN1104F | | _ | | 32.9 | 47 | 61.1 | |
| | RN1105F | | | | 1.54 | 2.2 | 2.86 | |
| | RN1106F | | | | 3.29 | 4.7 | 6.11 | |
| Resistor ratio | RN1101F ~1104F | | | | 0.9 | 1.0 | 1.1 | |
| | RN1105F | R1/R2 — | _ | 0.0421 | 0.0468 | 0.0515 | | |
| | RN1106F | | | | 0.09 | 0.1 | 0.11 | |

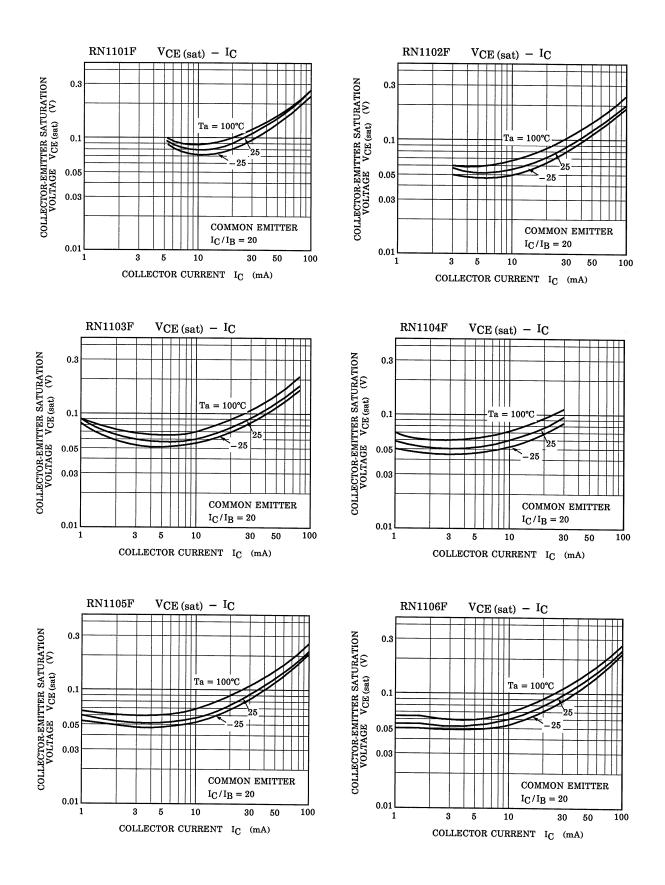
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| Type Name | Marking | | |
|-----------|------------------|--|--|
| RN1101F | Type Name X A | | |
| RN1102F | Type Name X B | | |
| RN1103F | Type Name X C | | |
| RN1104F | Type Name X D | | |
| RN1105F | Type Name X E | | |
| RN1106F | Type Name X F | | |

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20070701-EN GENERAL

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